



Dr. HanJin Lim

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Dr. Lim is a VP of Technology in the Process Development at Samsung Electronics since Dec. 2013. He received the Ph.D. degree in the department of Metallurgical Engineering from the University of Utah, Salt Lake City, UT in 1996 for his study on high T_c superconductor. From 1996 to 1998, he was a postdoctoral researcher in Stanford University, CA, where he worked on single crystal growth and MOCVD thin films. In 1998, he joined Samsung Electronics, Korea as a process development engineer. He has worked on exploring and demonstrating the feasibility of new integration schemes, high-k materials, and capacitor process modules for mass production of DRAM. In 2011, he researched at the Center for Integrated System in Stanford, CA as a visiting scholar. He is currently leading the R&D of various diffusion related processes for advanced semiconductor device scaling. His current research interest mainly focuses on new material exploration, novel fabrication technique, and novel integration design by using ALD/ALE/ASD processes for the advanced memory device. He co-chaired the Atomic Layer Deposition Conference in Songdo, Incheon in 2018 (ALD 2018).